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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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HSS104

Silicon Epitaxial Planar Diode for High Speed Switching



ADE-208-178B (Z)

Rev.2 Oct. 2000

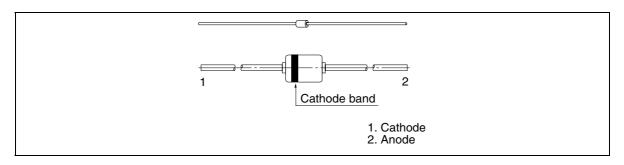
Features

- Short reverse recovery time and forward recovery time.
- Suitable for 5 mm pitch high speed automatically insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Туре No.	Cathode band	Package Code
HSS104	Blue	MHD

Pin Arrangement



HSS104

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Peak reverse voltage	V _{BM}	40	V
Reverse voltage	V _R	35	V
Average rectified current	I _o	110	mA
Peak forward current	I _{FM}	300	mA
Non-Repetitive peak forward surge current	I _{FSM} *	0.4	А
Power dissipation	Pd	300	mW
Junction temperature	Тј	175	°C
Storage temperature	Tstg	-65 to +175	°C

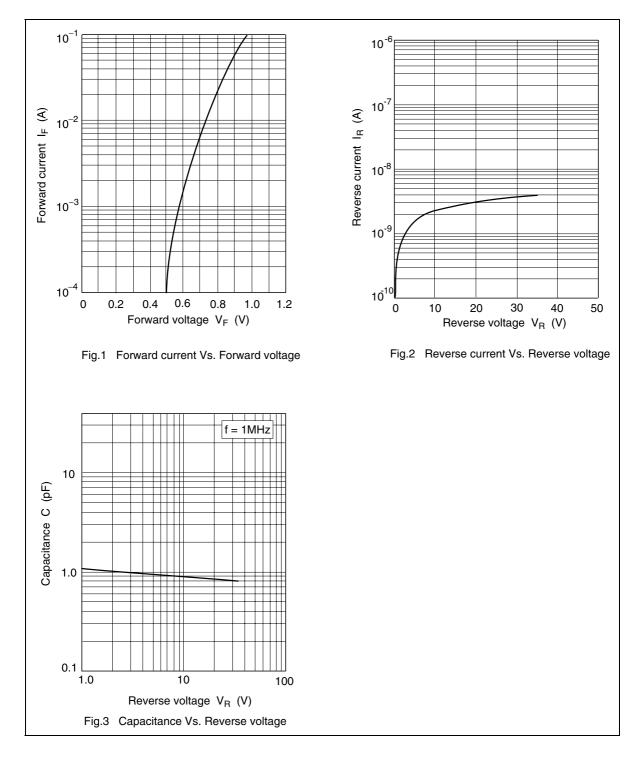
Note: Within 1s forward surge current.

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V _F	_	_	1.2	V	I _F = 100 mA
Reverse current	I _R	_	_	0.5	μA	V _R = 35 V
Capacitance	С	_	_	3.0	pF	$V_{_{\rm B}} = 0.5 \text{ V}, \text{ f} = 1 \text{ MHz}$
Reverse recovery time	t _{rr}	_	_	3.0	ns	$I_{_{\rm F}}$ = 10 mA, $V_{_{\rm R}}$ = 6 V, $R_{_{\rm L}}$ = 50 Ω

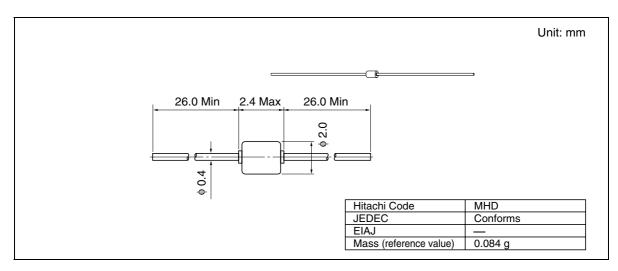
Main Characteristic



RENESAS

HSS104

Package Dimensions





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